

GaAlAs T-1 PACKAGE INFRARED EMITTING DIODE

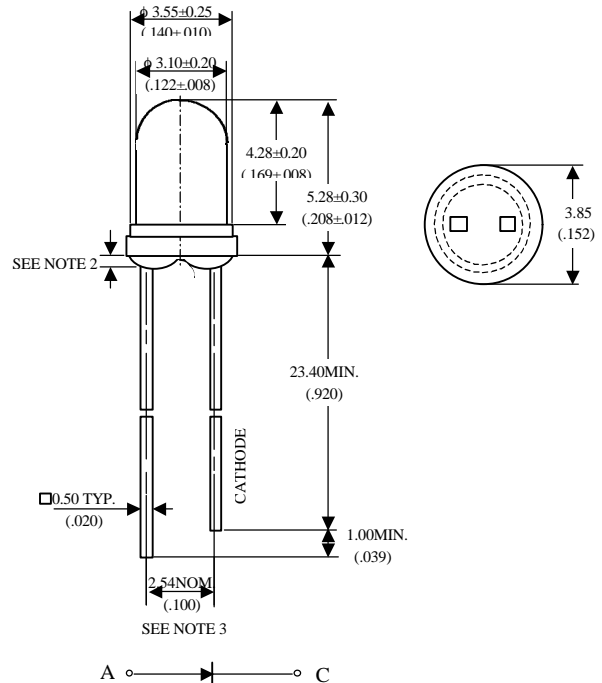
MIE-324L3

Description

The MIE-324L3 is an infrared emitting diode in GaAlAs on GaAlAs technology molded in water clear plastic package.

Package Dimensions

Unit : mm (inches)



Features

- High radiant power and high radiant intensity
- Suitable for DC and high pulse current operation
- Standard T-1 ($\phi 3\text{mm}$) package, radiant angle: 40°
- Peak wavelength $\lambda_p = 880 \text{ nm}$
- Good spectral matching to si-photodetector

Notes :

1. Tolerance is $\pm 0.25 \text{ mm}$ (0.010") unless otherwise noted.
2. Protruded resin under flange is 1.5 mm (0.059") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A = 25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	120	mW
Peak Forward Current(300pps,10 μ s pulse)	1	A
Continuous Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to $+100^\circ\text{C}$	
Storage Temperature Range	-55°C to $+100^\circ\text{C}$	
Lead Soldering Temperature	260 $^\circ\text{C}$ for 5 seconds	

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Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Intensity	I _F =20mA	I _e		1.5		mW/sr
Forward Voltage	I _F =50mA	V _F		1.4	1.7	V
Reverse Current	V _R =5V	I _R			100	μA
Peak Wavelength	I _F =20mA	λ _p		880		nm
Spectral Bandwidth	I _F =20mA	Δλ		80		nm
View Angle	I _F =20mA	2θ _{1/2}		40		deg .

Typical Optical-Electrical Characteristic Curves

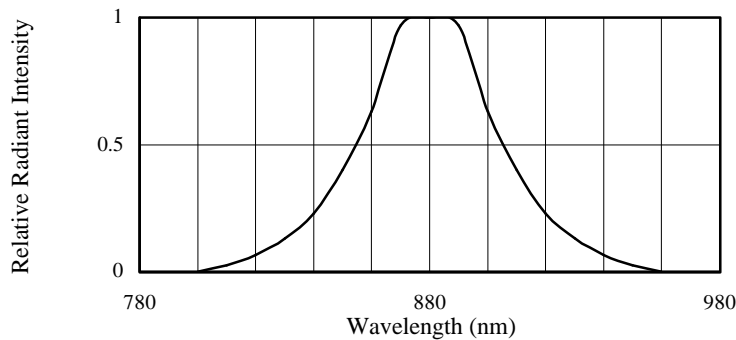


FIG.1 SPECTRAL DISTRIBUTION

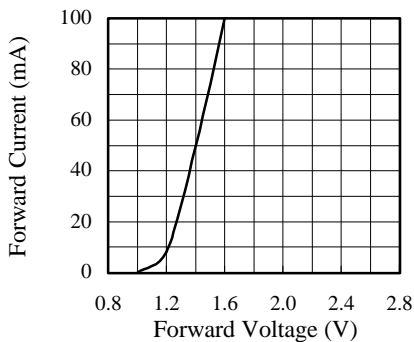


FIG.3 FORWARD CURRENT VS. FORWARD VOLTAGE

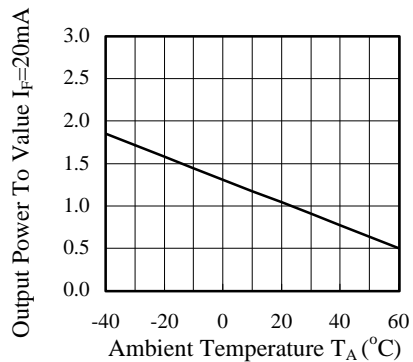


FIG.4 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

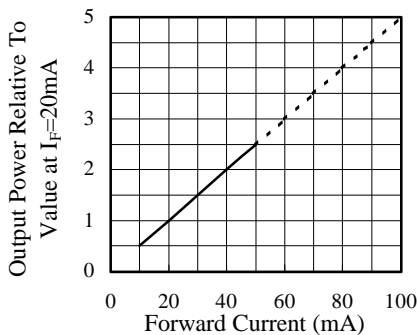


FIG.5 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

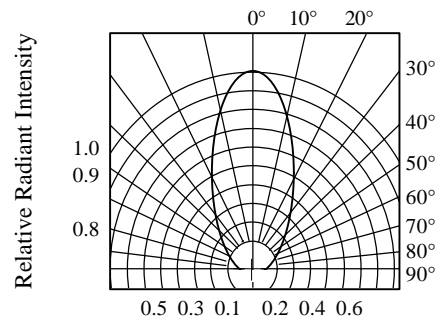


FIG.5 RADIATION DIAGRAM